

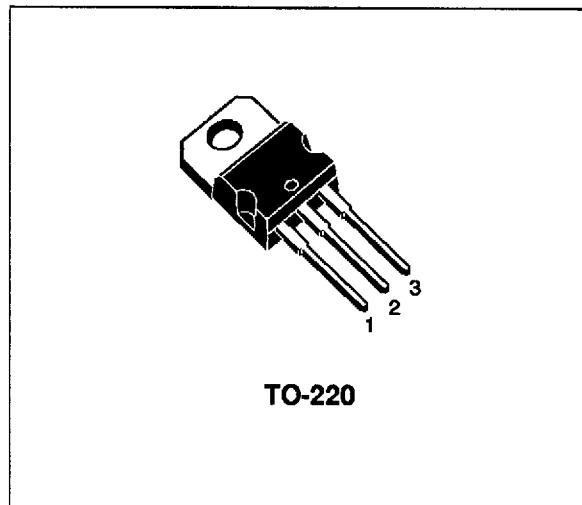
COMPLEMENTARY SILICON POWER TRANSISTORS

- BD908, BD909, BD910, BD911 AND BD912
SGS-THOMSON PREFERRED SALESTYPES

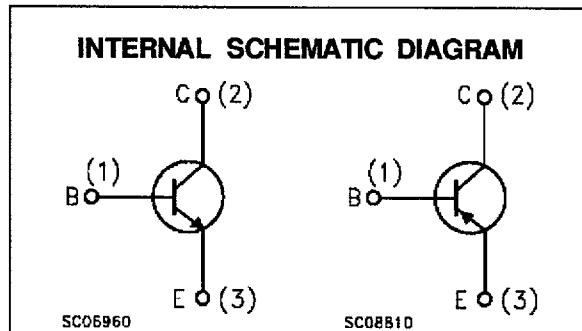
DESCRIPTION

The BD707, BD709, and BD711 are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intended for use in power linear and switching applications.

The complementary PNP types are BD908, BD910, and BD912 respectively.



TO-220



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	BD907	BD909	BD911	
		PNP	BD908	BD910	BD912	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		60	80	100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		60	80	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)			5		V
I_E, I_C	Collector Current			15		A
I_B	Base Current			5		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$			90		W
T_{stg}	Storage Temperature			-65 to 150		°C
T_j	Max. Operating Junction Temperature			150		°C

For PNP types voltage and current values are negative.

BD907/BD908/BD909/BD910/BD911/BD912

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.67	$^{\circ}\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	for BD907/908	$V_{CB} = 60\text{ V}$			500	μA
		for BD909/910	$V_{CB} = 80\text{ V}$			500	μA
		for BD911/912	$V_{CB} = 100\text{ V}$			500	μA
		$T_{case} = 150^{\circ}\text{C}$					
		for BD907/908	$V_{CB} = 60\text{ V}$			5	mA
		for BD909/910	$V_{CB} = 80\text{ V}$			5	mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	for BD907/908	$V_{CB} = 30\text{ V}$			1	mA
		for BD909/910	$V_{CB} = 40\text{ V}$			1	mA
		for BD911/912	$V_{CB} = 50\text{ V}$			1	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$				1	mA
$V_{CEO(sus)}$ *	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100\text{ mA}$	for BD907/908	60			V
			for BD909/910	80			V
			for BD911/912	100			V
$V_{CE(sat)}$ *	Collector-Emitter Saturation Voltage	$I_C = 5\text{ A}$	$I_B = 0.5\text{ A}$			1	V
		$I_C = 10\text{ A}$	$I_B = 2.5\text{ A}$			3	V
$V_{BE(sat)}$ *	Base-Emitter Saturation Voltage	$I_C = 10\text{ A}$	$I_B = 2.5\text{ A}$			2.5	V
V_{BE} *	Base-Emitter Voltage	$I_C = 5\text{ A}$	$V_{CE} = 4\text{ V}$			1.5	V
h_{FE} *	DC Current Gain	$I_C = 0.5\text{ A}$	$V_{CE} = 4\text{ V}$	40		250	
		$I_C = 5\text{ A}$	$V_{CE} = 4\text{ V}$	15		150	
		$I_C = 10\text{ A}$	$V_{CE} = 4\text{ V}$	5			
f_T	Transition frequency	$I_C = 0.5\text{ A}$	$V_{CE} = 4\text{ V}$	3			MHz

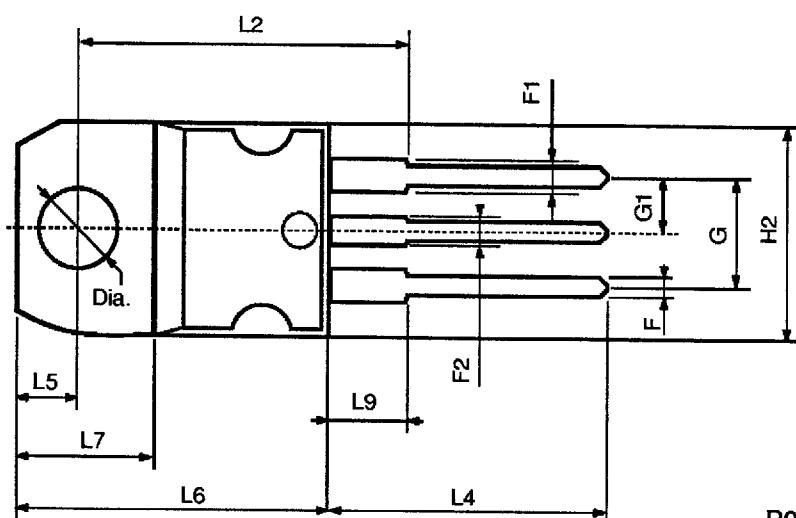
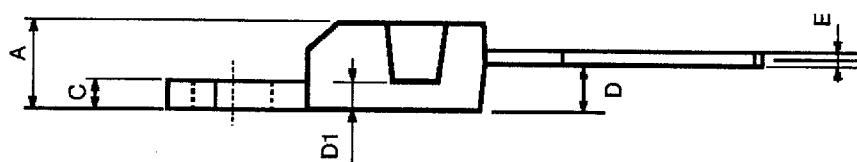
* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

** Value for which $I_C = 3.3\text{ A}$ at $V_{CE} = 2\text{V}$.

For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C